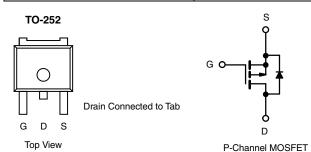


PRODUCT SUMMARY				
V _{DS} (V)	- 80			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.028			
I _D (A)	- 48			
Configuration	Single			



FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- AEC-Q101 Qualifiedd
- 100 % R_q and UIS Tested



ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD50P08-28-GE3

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage		V_{DS}	- 80	V		
Gate-Source Voltage	V _{GS}	± 20	V			
Continuous Dunis Comment	T _C = 25 °C	1	- 48			
Continuous Drain Current	T _C = 125 °C	- I _D	- 28			
Continuous Source Current (Diode Conduction) ^a	I _S	- 50	Α			
Pulsed Drain Current ^b	I _{DM}	- 190				
Single Pulse Avalanche Current	l 0.1 mll	I _{AS}	- 45			
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	100	mJ		
Mariana Barran Birain ationsh	T _C = 25 °C	- P _D	136	W		
Maximum Power Dissipation ^b	T _C = 125 °C		45] vv		
Operating Junction and Storage Temperature Range	e	T _J , T _{stg}	- 55 to + 175	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	50	°C/W		
Junction-to-Case (Drain)		R _{thJC}	1.1	G/ VV		

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



SPECIFICATIONS ($T_C = 25 ^{\circ}C$, PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} :	V _{GS} = 0, I _D = - 250 μA		_	-	.,
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V _{DS} = V _{GS} , I _D = - 250 μA		- 3.0	- 3.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
		V _{GS} = 0 V	V _{DS} = - 80 V	-	-	- 1	μΑ
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = - 80 V, T _J = 125 °C	-	-	- 50	
		V _{GS} = 0 V	V _{DS} = - 80 V, T _J = 175 °C	-	-	- 250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	$V_{DS} \le -5 V$	- 50	-	-	Α
		V _{GS} = - 10 V	I _D = - 12.5 A	-	0.023	0.028	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 12.5 A, T _J = 125 °C	-	-	0.049	Ω
		V _{GS} = - 10 V	I _D = - 12.5 A, T _J = 175 °C	-	-	0.061	
Forward Transconductance ^b	9 _{fs}	V _{DS} = -	- 15 V, I _D = - 12.5 A	-	32	-	S
Dynamic ^b							
Input Capacitance	C _{iss}		= 0 V V _{DS} = - 25 V, f = 1 MHz	-	4826	6035	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	343	430	
Reverse Transfer Capacitance	C _{rss}			-	224	280	
Total Gate Charge ^c	Qg			-	95	145	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 10 V	$V_{DS} = -40 \text{ V}, I_{D} = -12.5 \text{ A}$	-	19	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	26	-	
Gate Resistance	R _g		f = 1 MHz		3.47	5.21	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	15	23	
Rise Time ^c	t _r	V _{DD} =	$V_{DD} = -40 \text{ V}, R_{L} = 3.8 \Omega$		11	17	ns
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong$ - 10.5 A, V_{GEN} = - 10 V, R_g = 1 Ω		-	65	98	
Fall Time ^c	t _f			-	16	24	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	- 190	Α
Forward Voltage	V_{SD}	I _F = - 10 A, V _{GS} = 0			- 0.82	- 1.5	V

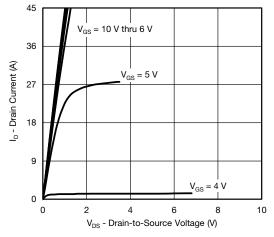
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

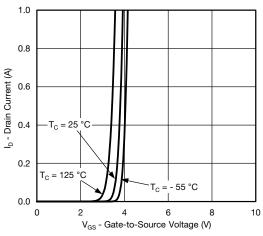
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



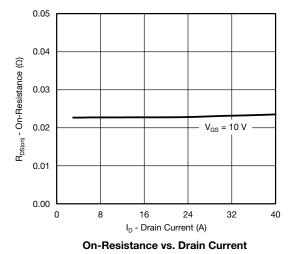
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

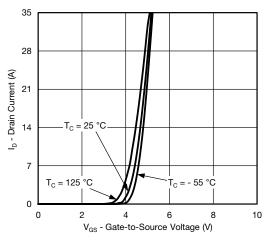


Output Characteristics

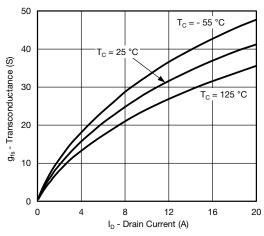


Transfer Characteristics

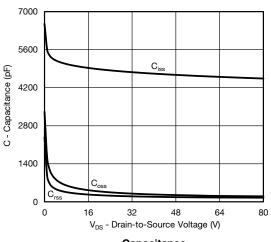




Transfer Characteristics



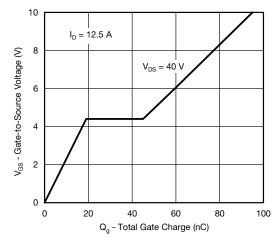
Transconductance



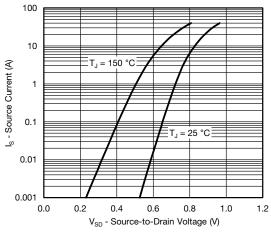
Capacitance



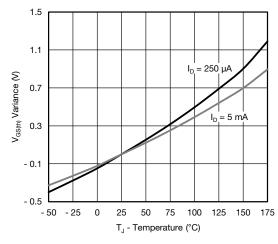
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



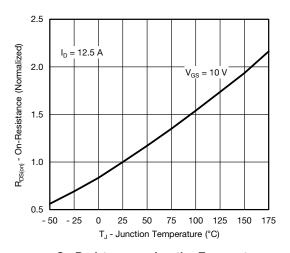
Gate Charge



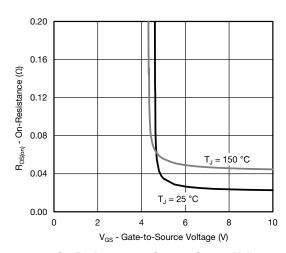
Source Drain Diode Forward Voltage



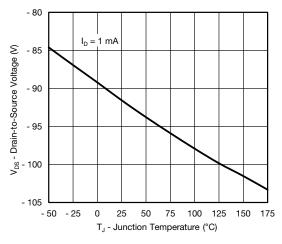
Threshold Voltage



On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

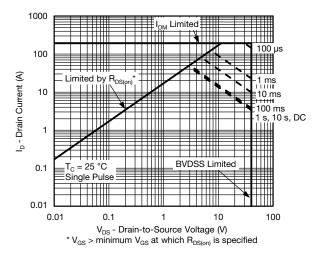


Drain Source Breakdown vs. Junction Temperature

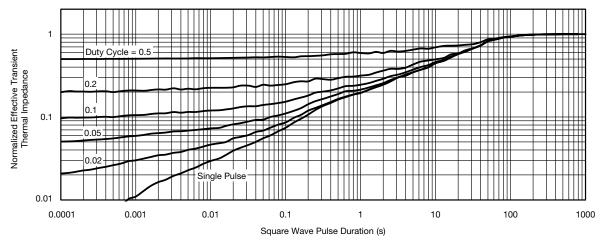
SQD50P08-28

Automotive P-Channel 80 V (D-S) 175 °C MOSFET

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)

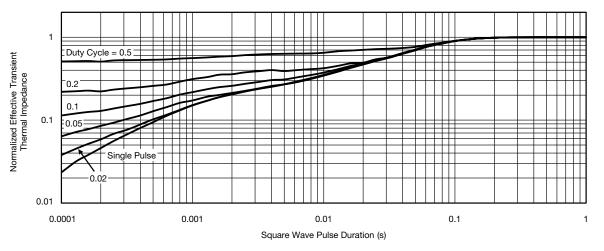


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)

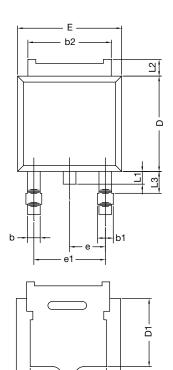


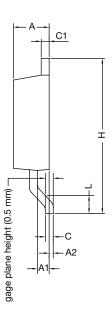
Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

TO-252AA CASE OUTLINE





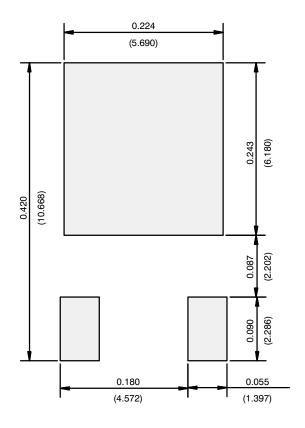
	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28	BSC	0.090 BSC		
e1	4.57 BSC		0.180 BSC		
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

• Dimension L3 is for reference only.

SQD50P08-28 Automotive P-Channel

80 V (D-S) 175 °C MOSFET

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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